

DMTH3002LPS-13 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number DMTH3002LPS-13-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMTH3002LPS-13

Description MOSFET N-CH 30V 100A PWRDI5060-8

Detailed Description N-Channel 30 V 100A (Tc) 1.2W (Ta), 136W (Tc) Surf

ace Mount PowerDI5060-8



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMTH3002LPS-13	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	100A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	1.6mOhm @ 25A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 1mA	77 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±16V	5000 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	1.2W (Ta), 136W (Tc)
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
PowerDI5060-8	8-PowerTDFN
Base Product Number:	
DMTH3002	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





30V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
30V	$1.6 \text{m}\Omega$ @ $V_{GS} = 10V$	240A

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

Applications

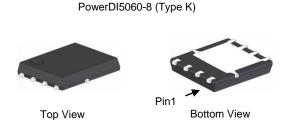
- DC-DC Converters
- Load Switch

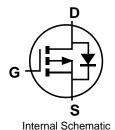
Features

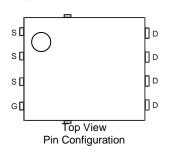
- Thermally Efficient Package Cooler Running Applications
- <1.1mm Package Profile Ideal for Thin Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI5060-8 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)







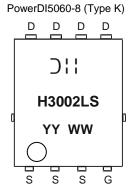
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH3002LPS-13	PowerDI5060-8 (Type K)	2,500/Tape & Reel

Notes:

- $1. \; EU \; Directive \; 2002/95/EC \; (RoHS) \; \& \; 2011/65/EU \; (RoHS \; 2) \; compliant. \; All \; applicable \; RoHS \; exemptions \; applied.$
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



☐ Hanufacturer's Marking

H3002LS = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 17 = 2017)

WW = Week Code (01 to 53)



Maximum Ratings (@ $T_C = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±16	V
Continuous Drain Current, V _{GS} = 10V (Note 7)	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	240 240	А
Maximum Continuous Body Diode Forward Current (Note 7)			I _S	100	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	400	Α
Pulsed Continuous Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I _{SM}	400	Α
Avalanche Current, L=3mH (Note 8)			I _{AS}	15	Α
Avalanche Energy, L=3mH (Note 8)			E _{AS}	700	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	103	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	51	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P_{D}	136	W
Thermal Resistance, Junction to Case (Note 7)		R ₀ JC	1.1	°C/W
Operating and Storage Temperature Range		$T_{J_{i}}T_{STG}$	-55 to +175	°C

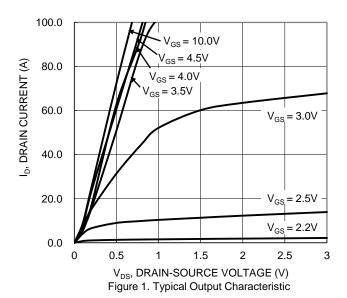
Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

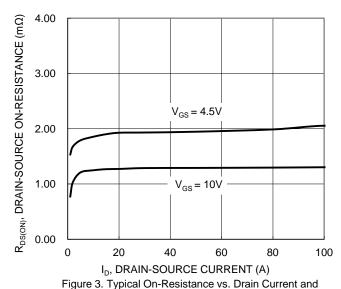
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	1	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance	D	-	1.25	1.6	mΩ	$V_{GS} = 10V, I_D = 25A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	l	2	2.5	11177	$V_{GS} = 4.5V, I_D = 25A$	
Diode Forward Voltage	V_{SD}	-	0.8	1.1	V	$V_{GS} = 0V, I_S = 25A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{ISS}	1	5,000			V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	1	2,660		pF		
Reverse Transfer Capacitance	C _{RSS}	-	300	_		I = IIVII IZ	
Gate Resistance	R_{G}	1	0.75		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_G	-	37	_			
Total Gate Charge (V _{GS} = 10V)	Q _G	_	77	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q_{GS}	_	10	_	IIC	$V_{DS} = 15V, I_{D} = 25A$	
Gate-Drain Charge	Q_{GD}	_	14	_			
Turn-On Delay Time	t _{D(ON)}	_	21	_			
Turn-On Rise Time	t _R	_	45	_		$V_{DD} = 15V, V_{GS} = 4.5V,$ $I_{D} = 25A, R_{G} = 4.7\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	32	_	ns		
Turn-Off Fall Time	t _F	_	26	_			
Body Diode Reverse Recovery Time	t _{RR}	_	44	_	ns	1 15A di/dt 100A/up	
Body Diode Reverse Recovery Charge	Q_{RR}	_	52	_	nC	$I_S = 15A$, di/dt = 100A/ μ s	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.







Gate Voltage

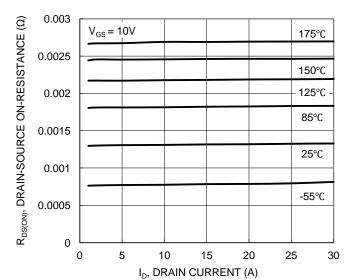
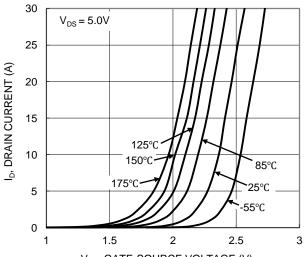


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

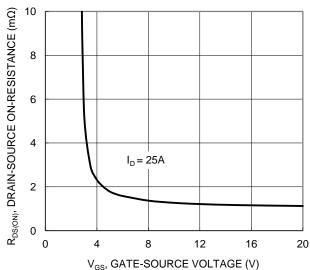


Figure 4. Typical Transfer Characteristic

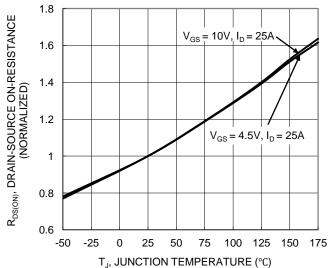


Figure 6. On-Resistance Variation with Temperature



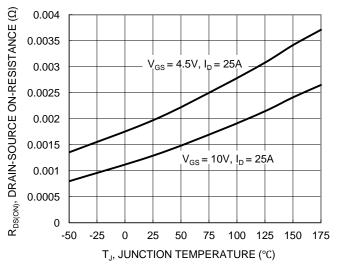


Figure 7. On-Resistance Variation with Temperature

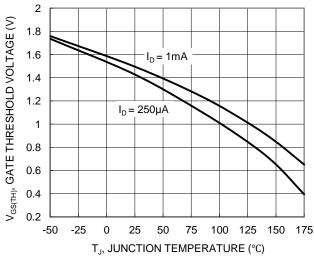


Figure 8. Gate Threshold Variation vs. JunctionTemperature

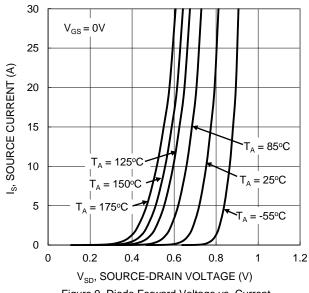


Figure 9. Diode Forward Voltage vs. Current

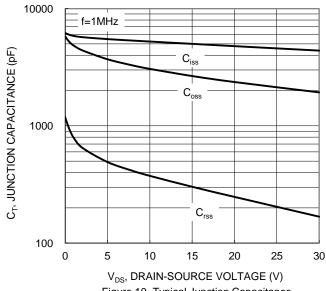
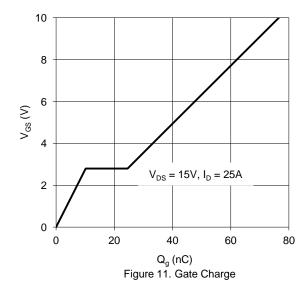


Figure 10. Typical Junction Capacitance



1000 100 DRAIN CURRENT (A) 10 $= 100 \mu s$ $T_{J(max)} = 175$ °C ئ T_C = 25°C V_{GS} = 10V Single Pulse DUT on 1 * MRP Board 0.01 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12 SOA, Safe Operation Area



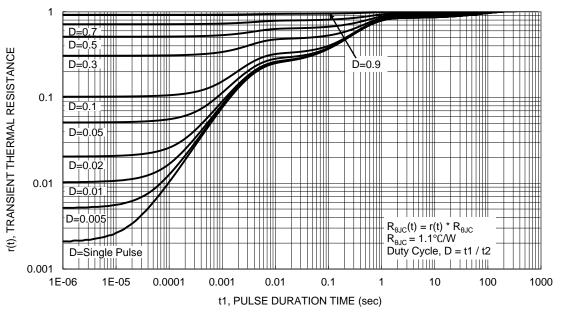


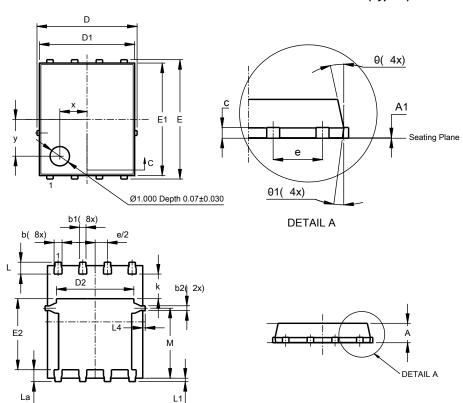
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)

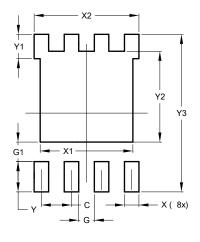


PowerDI5060-8 (Type K)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05	0.02	
b	0.33	0.51	0.41	
b1	0.300	0.366	0.333	
b2	0.20	0.35	0.25	
С	0.23	0.33	0.277	
D	5	.15 BS0		
D1	4.85	4.95	4.90	
D2	-	-	3.98	
E	6	.15 BS0		
E1	5.75	5.85	5.80	
E2	3.56	3.725	3.66	
Е	1	.27BSC)	
k	-	-	1.27	
L	0.51	0.71	0.61	
La	0.51	0.675	0.61	
L1	0.05	0.20	0.175	
L4	-	-	0.125	
М	3.50	3.71	3.605	
X	-	-	1.400	
у	-	-	1.900	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	3.910		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6 610		



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com



OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com

















Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com